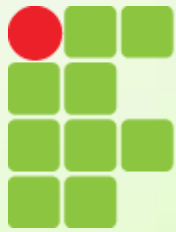
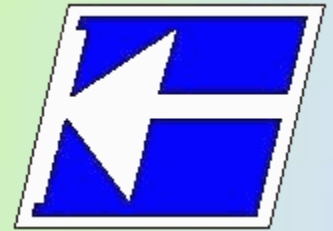


**Instituto Federal de Educação, Ciência e Tecnologia de Santa Catarina**



**INSTITUTO FEDERAL  
SANTA CATARINA**

**Departamento Acadêmico de Eletrônica  
Eletrônica Básica e Projetos Eletrônicos**



# **Características de Diodos e Análise de Circuitos com Diodos**

**Prof. Clóvis Antônio Petry.**

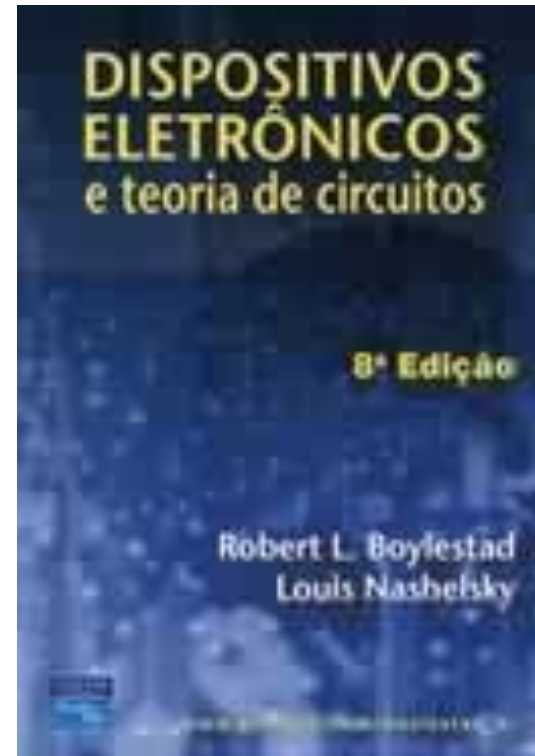
**Florianópolis, fevereiro de 2009.**

# Nesta aula

## **Seqüência de conteúdos:**

1. Características dos diodos;
2. Modelos representativos de diodos.
3. Análise de circuitos com diodos.

# Bibliografia



# Características dos diodos

## As principais características (grandezas) são:

1. Corrente máxima direta ( $I_F$  ou  $I_o$ );
2. Tensão de ruptura reversa:
  - VRRM = Tensão de pico inverso repetitivo;
  - VRWM = Tensão de pico inverso de trabalho;
  - VR = Tensão de bloqueio CC.
3. Queda de tensão direta ( $v_F$ );
4. Corrente reversa máxima ( $I_R$ ).
5. Entre outras ....

# Características dos diodos

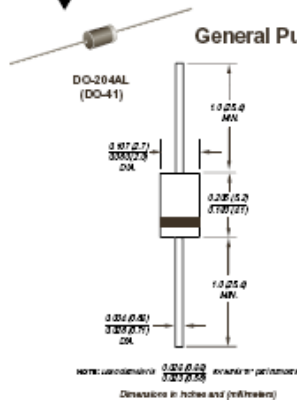


1N4001 thru 1N4007

Vishay Semiconductors  
formerly General Semiconductor

## General Purpose Plastic Rectifier

Reverse Voltage  
50 to 1000V  
Forward Current 1.0A



### Features

- Plastic package has Underwriters Laboratories Rammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- Low reverse leakage
- High forward surge capability
- High temperature soldering guaranteed 350°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

### Mechanical Data

Case: JEDEC DO-204AL, molded plastic body  
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026  
Polarity: Color band denotes cathode and  
Mounting Position: Any  
Weight: 0.012 oz., 0.3 g

### Maximum Ratings & Thermal Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Parameter	Symb.	1N4001	1N4002	1N4003	1N4004	1N4005	1N4006	1N4007	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
* Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
* Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A = 75^\circ\text{C}$	$I_{F(AV)}$				1.0				A
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) $T_A = 75^\circ\text{C}$	$I_{FSM}$				30				A
* Maximum full load reverse current, full cycle average 0.375" (9.5mm) lead length $T_A = 75^\circ\text{C}$	$I_{R(AV)}$				30				$\mu\text{A}$
Typical thermal resistance <sup>(1)</sup>	$R_{\theta JA}$ $R_{\theta JL}$				50 25				*°C/W
* Maximum DC blocking voltage temperature	$T_A$				+150				V
* Operating junction and storage temperature range	$T_J, T_{STG}$				-50 to +175				*°C

### Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum instantaneous forward voltage at 1.0A	$V_F$				1.1				V
* Maximum DC reverse current at rated DC blocking voltage $T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	$I_R$				5.0 50				$\mu\text{A}$
Typical junction capacitance at 4.0V, 1MHz	$C_J$				15				pF

Note: (1) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted \*JEDEC registered value

Bulletin PD-20731 rev. C 12/05

International  
**IOR** Rectifier

Ultrafast Rectifier

MUR820  
MURB820  
MURB820-1

### Features

- Ultrafast Recovery Time
- Low Forward Voltage Drop
- Low Leakage Current
- 175°C Operating Junction Temperature

$t_r = 25\text{ns}$   
 $I_{F(AV)} = 8\text{Amp}$   
 $V_F = 200\text{mV}$

### Description/Applications

International Rectifier's MUR series are the state of the art ultra fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultra fast recovery time. The planar structure and the platinum dopant life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drives. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

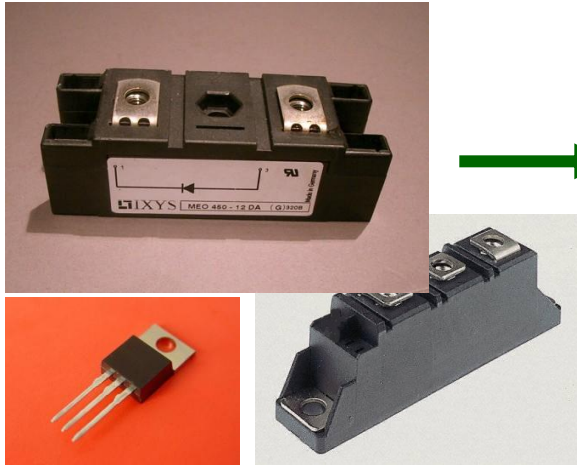
### Absolute Maximum Ratings

Parameters	Max	Units
$V_{RRM}$ Peak Repetitive Peak Reverse Voltage	200	V
$I_{F(AV)}$ Average Rectified Forward Current	8	A
Total Device, (Rated $V_F$ ), $T_C = 150^\circ\text{C}$		
$I_{FSM}$ Non Repetitive Peak Surge Current	100	
$I_{FR}$ Peak Repetitive Forward Current (Rated $V_F$ , Square wave, 20 kHz), $T_C = 150^\circ\text{C}$	18	
$T_J, T_{STG}$ Operating Junction and Storage Temperature	-55 to 175	*°C

### Case Styles



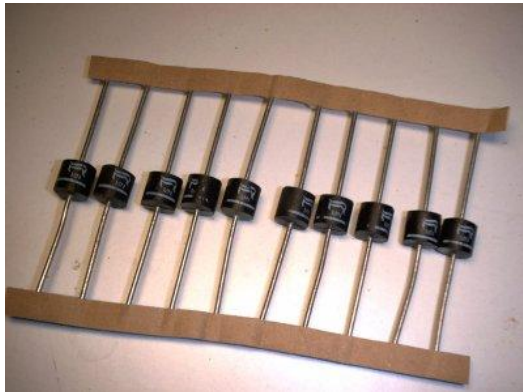
# Características dos diodos



Diodos de potência

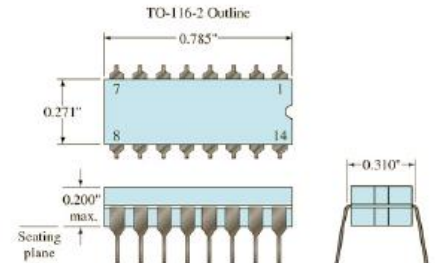
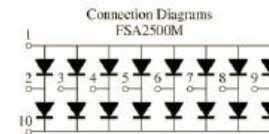


Diodos de sinal

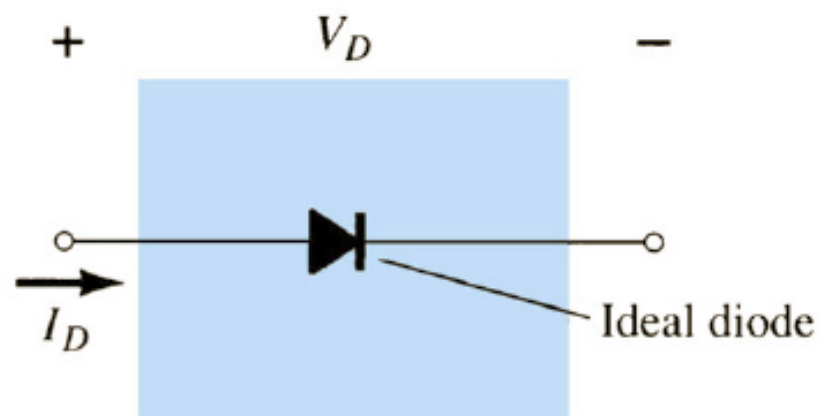
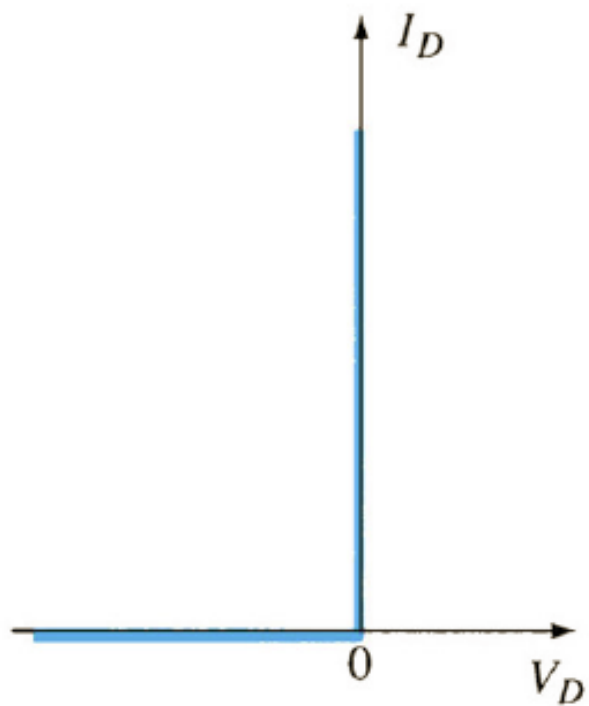


Diodos de uso geral

Circuitos integrados de diodos



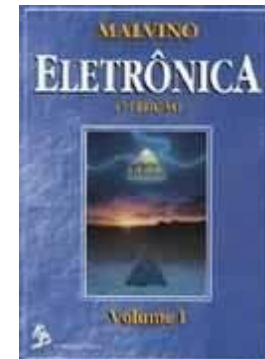
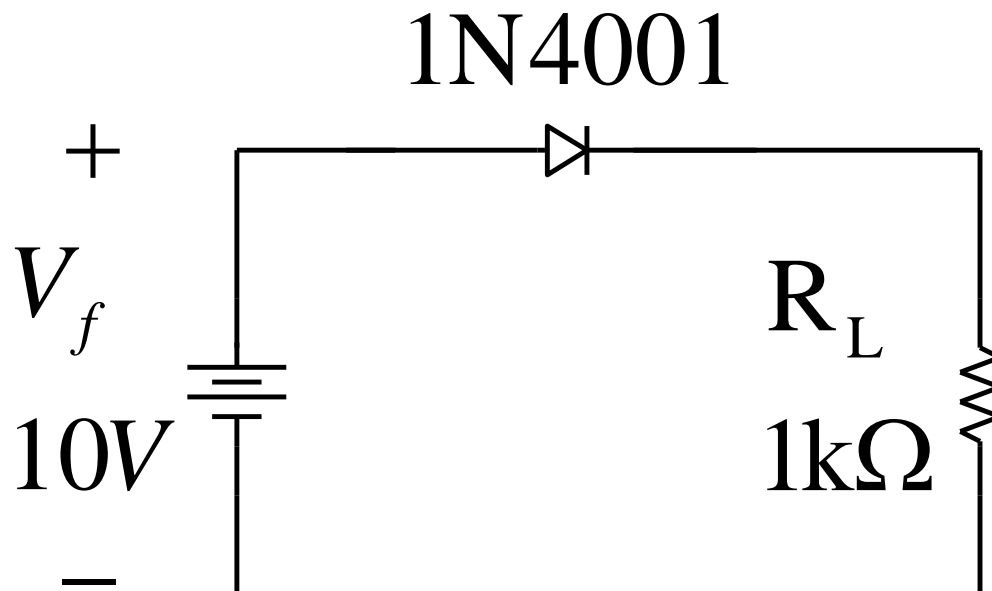
# Modelo ideal do diodo



# Modelo ideal do diodo

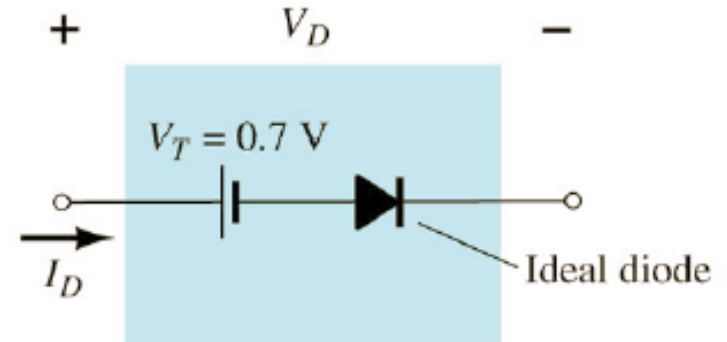
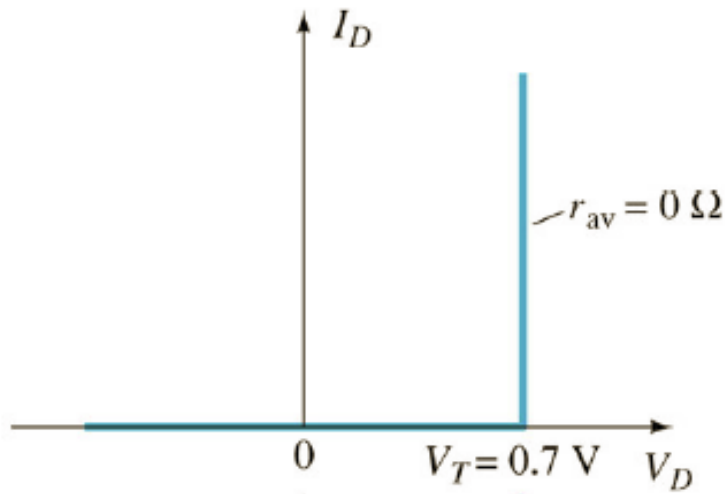
## Exemplo 3.4 – Eletrônica, vol. 1:

- Use a aproximação do diodo ideal para calcular a corrente de carga, a tensão na carga, a potência na carga, a potência no diodo e a potência total no circuito da figura abaixo.



Exemplo 3.4 do Malvino.

# Modelo simplificado do diodo

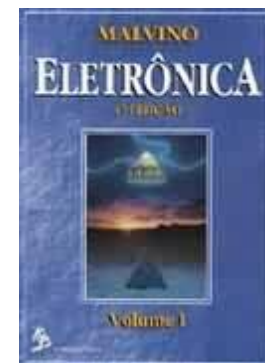
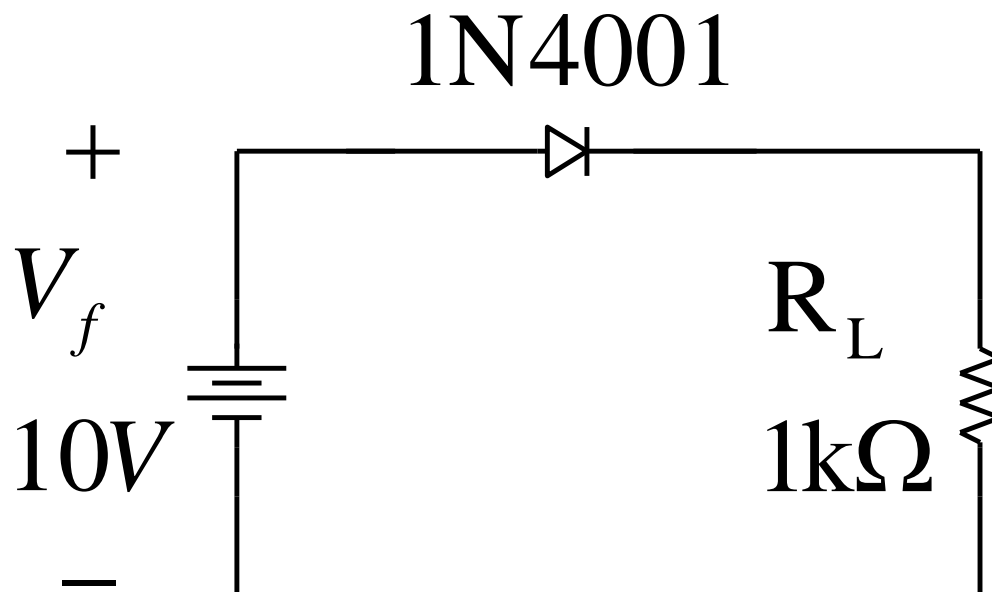


Exemplo 3.5 do Malvino.

# Modelo simplificado do diodo

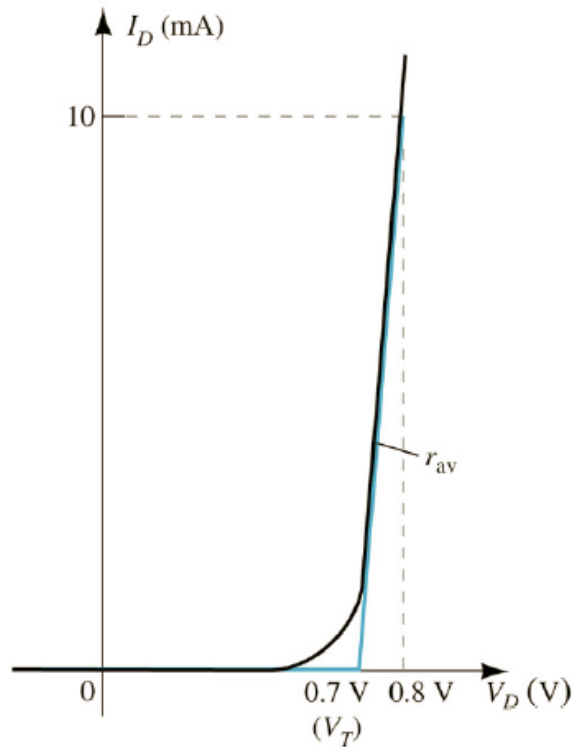
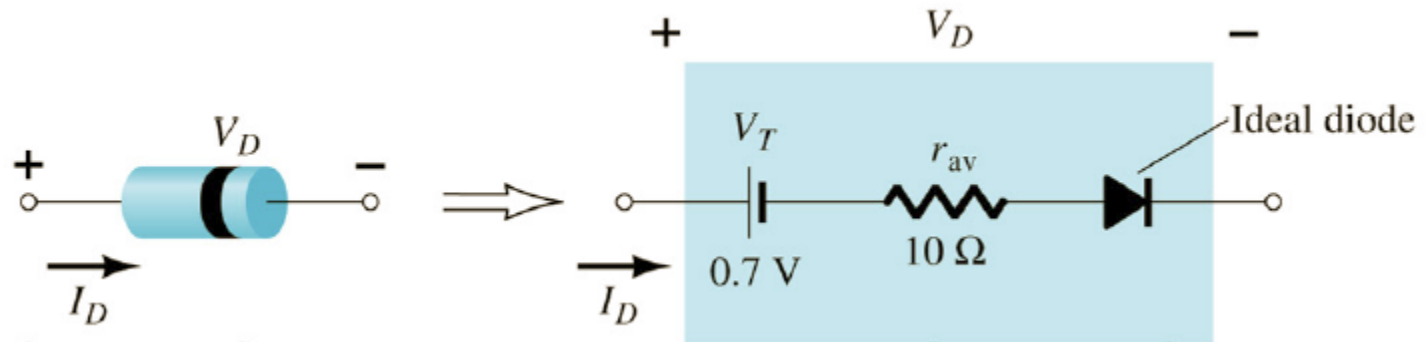
## Exemplo 3.5 – Eletrônica, vol. 1:

- Use a segunda aproximação para calcular a corrente na carga, a tensão na carga, a potência na carga, a potência no diodo e a potência total para o circuito abaixo.



Exemplo 3.5 do Malvino.

# Modelo linear por partes do diodo

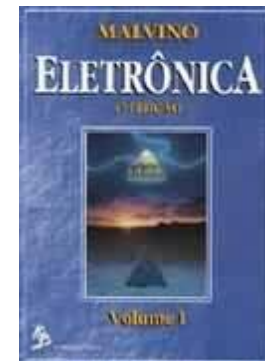
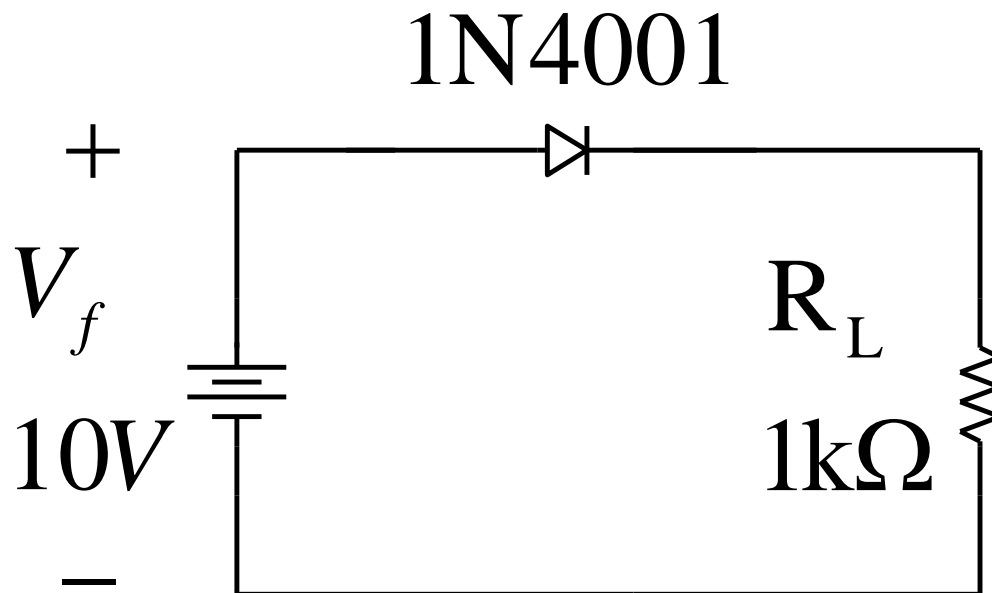


Exemplo 3.6 do Malvino.

# Modelo linear por partes do diodo

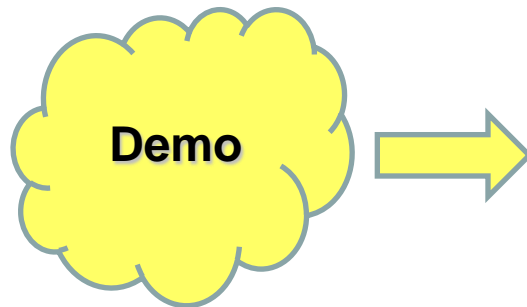
## Exemplo 3.6 – Eletrônica, vol. 1:

- Use a terceira aproximação para calcular a corrente na carga, a tensão na carga, a potência na carga, a potência no diodo e a potência total para o circuito abaixo. A resistência de corpo do diodo 1N4001 é  $0,23\Omega$ .



Exemplo 3.6 do Malvino.

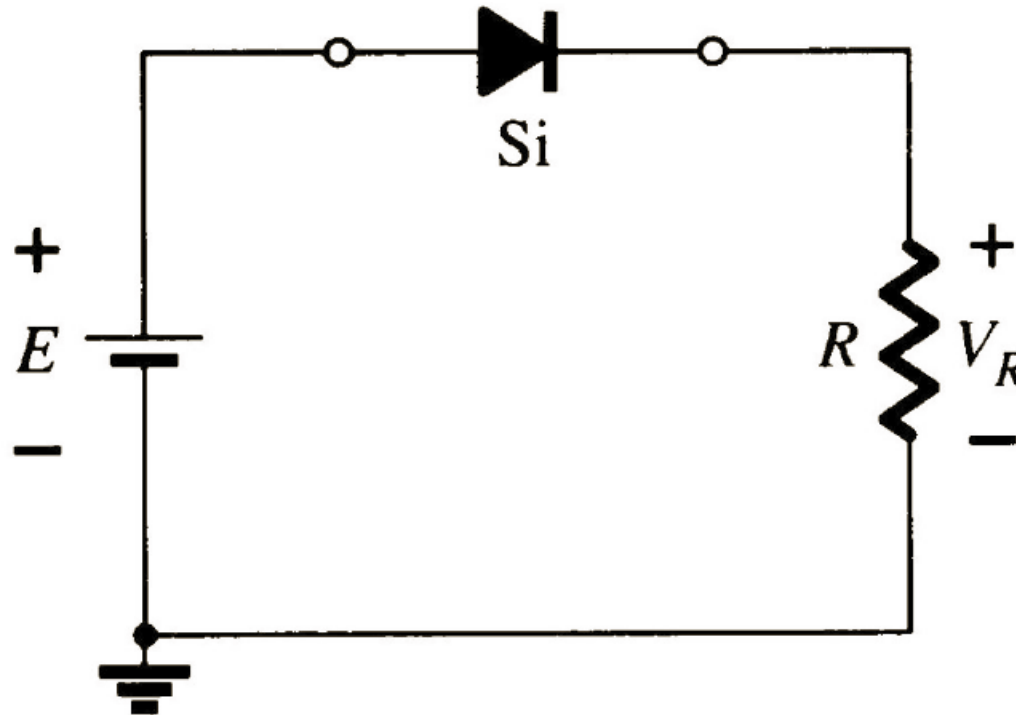
# Modelos representativos de diodos



Demo:

- Circuito série com diodo.

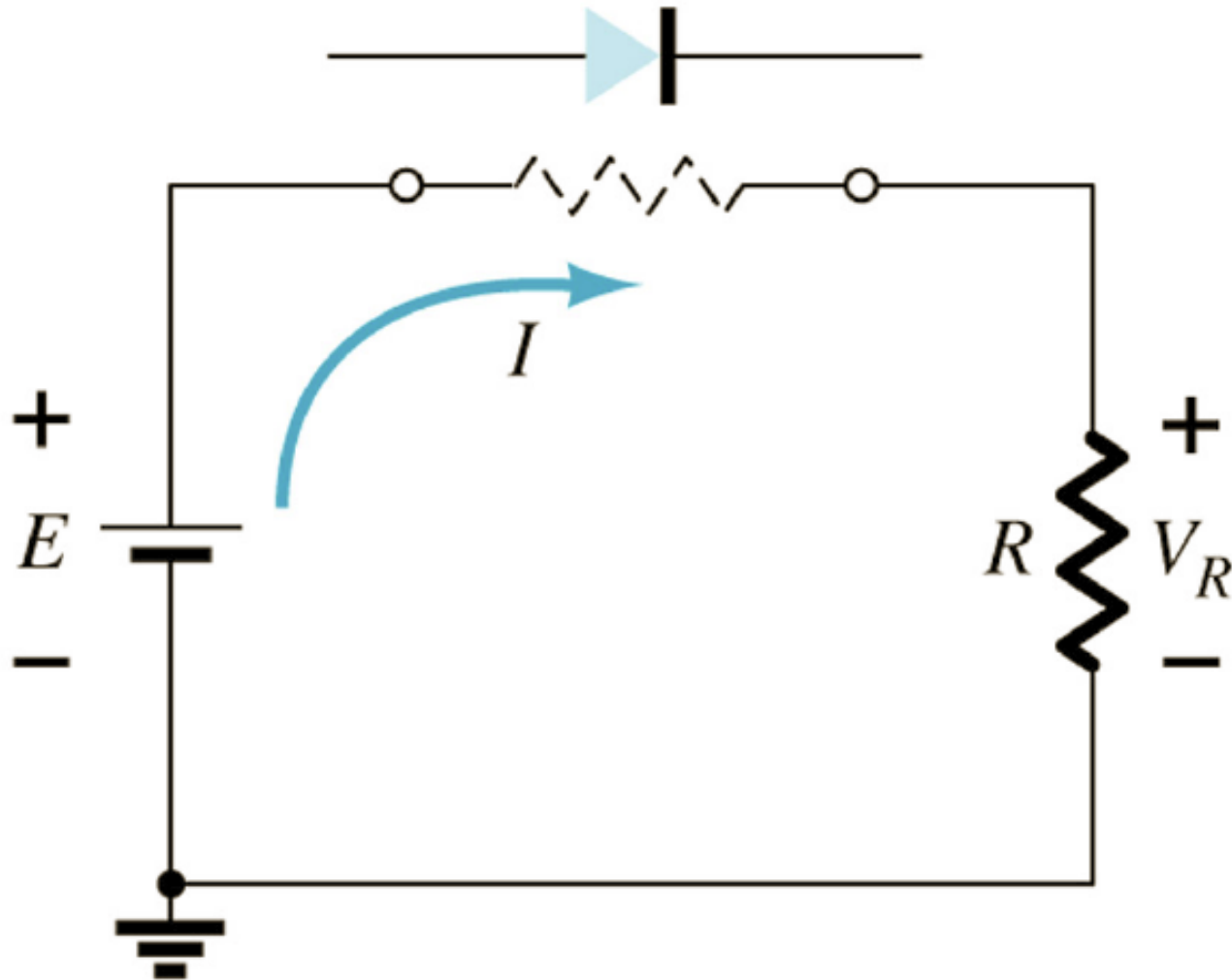
# Circuitos série de diodos



Em geral, um diodo está no estado ligado (ON) se a corrente estabelecida pelas fontes é tal que o seu sentido coincide com o da seta do símbolo do diodo.

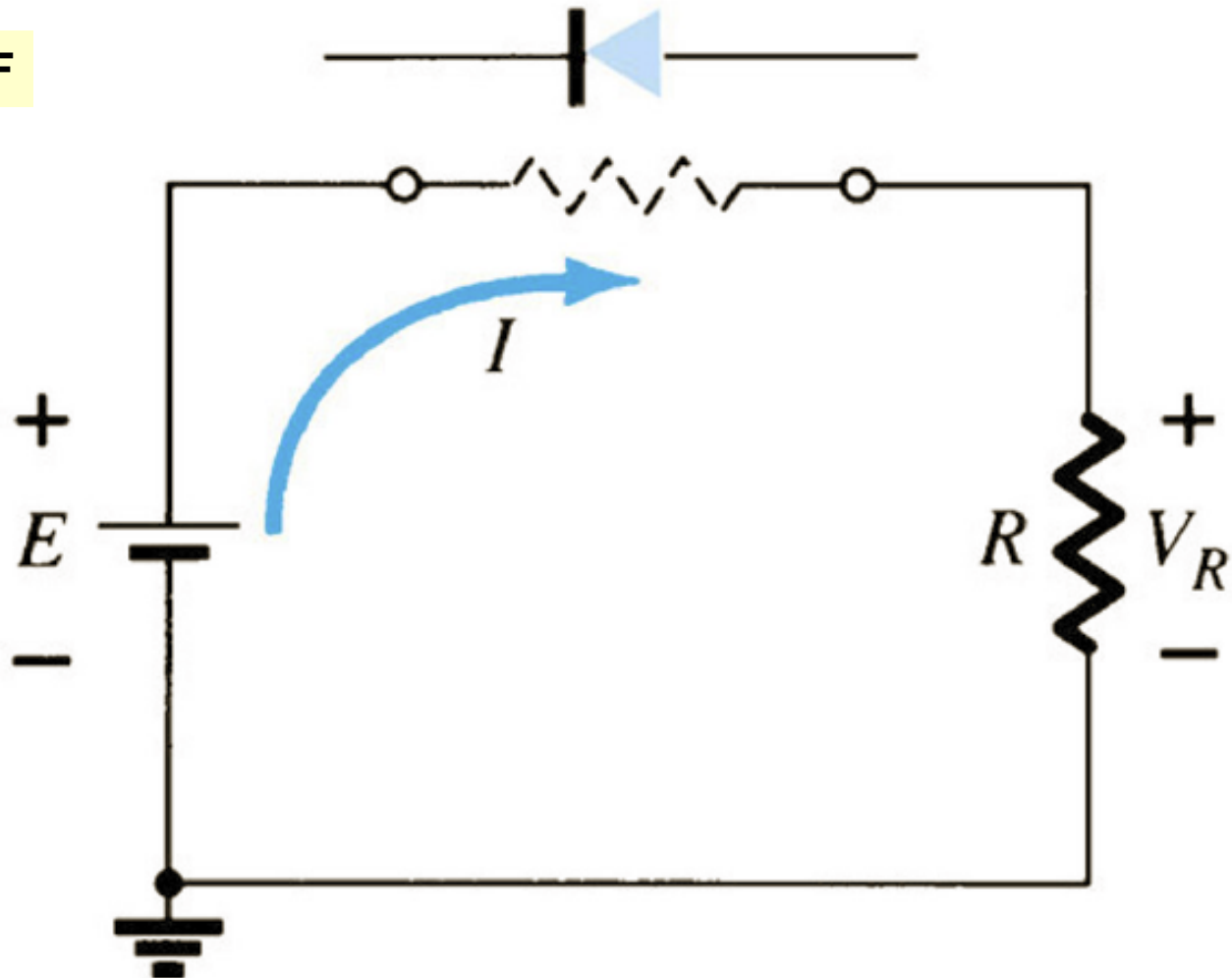
# Circuitos série de diodos

Diodo ON

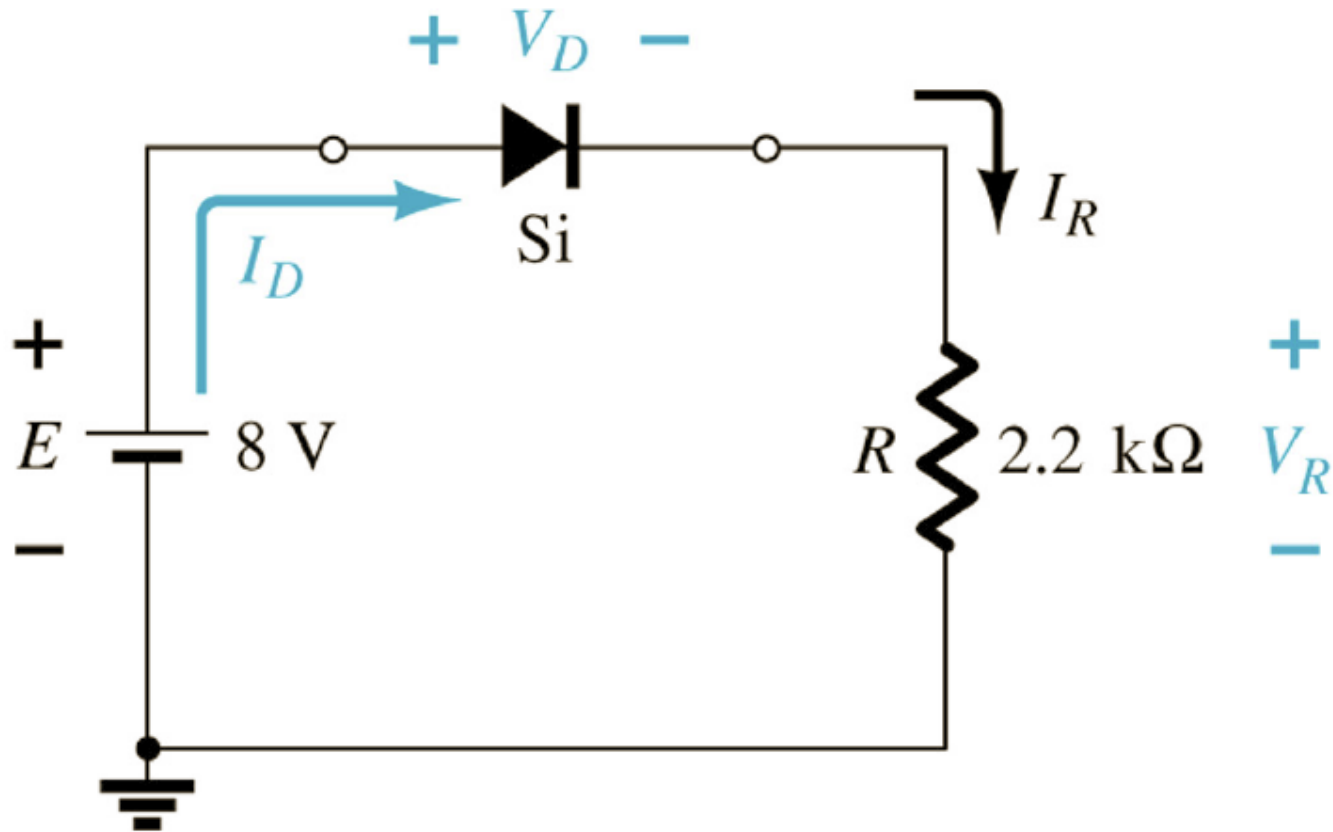


# Circuitos série de diodos

Diodo OFF



# Circuitos série de diodos



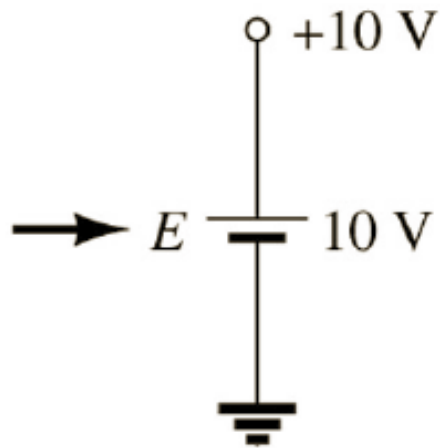
a) Diodo está ON ou OFF?

b) Determine  $V_D$ ,  $V_R$  e  $I_D$ .

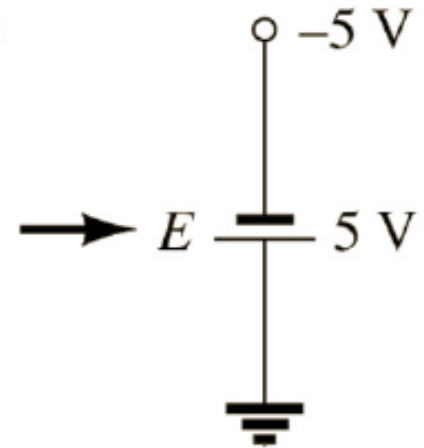
# Circuitos série de diodos

Importante: notação de fontes.

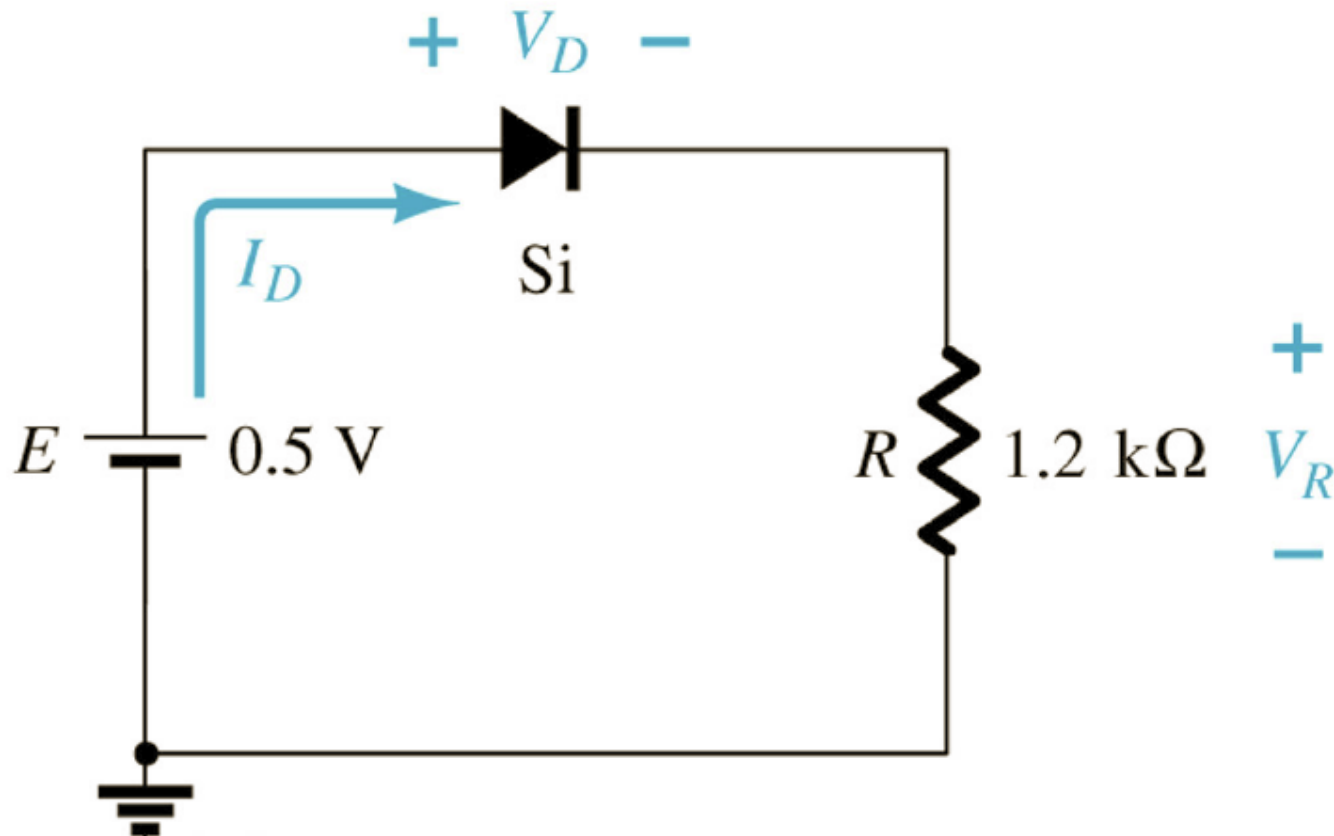
$$E = +10 \text{ V} \circ$$



$$E = -5 \text{ V} \circ$$



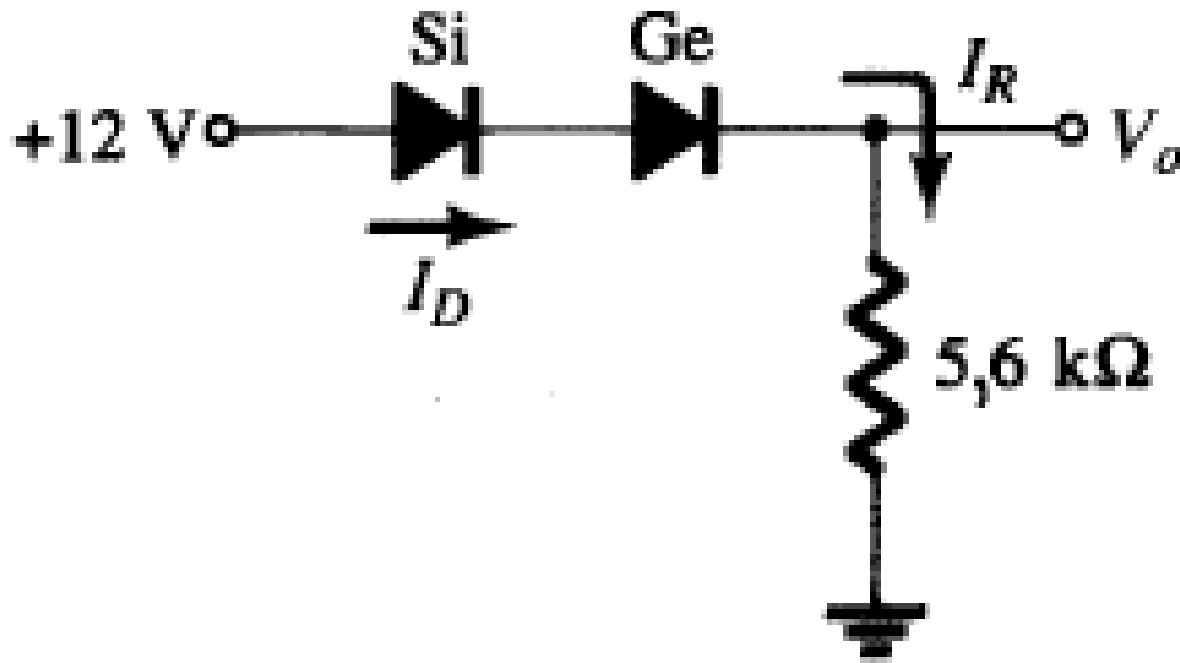
# Circuitos série de diodos



a) Diodo está ON ou OFF?

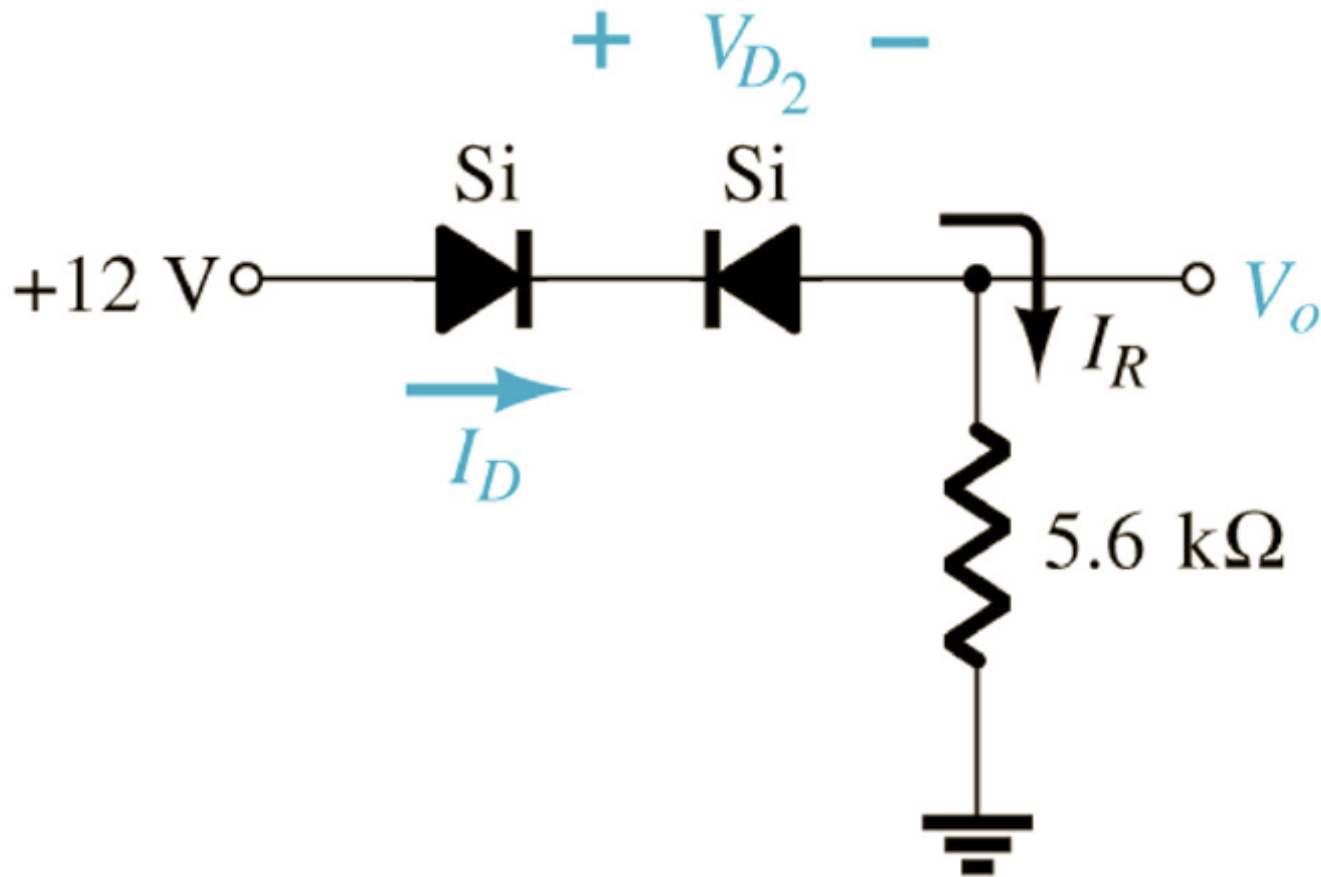
b) Determine  $V_D$ ,  $V_R$  e  $I_D$ .

# Circuitos série de diodos



- Quem está conduzindo (ON) e quem está bloqueado (OFF)?
- Determine  $V_o$ ,  $I_R$  e  $I_o$ .

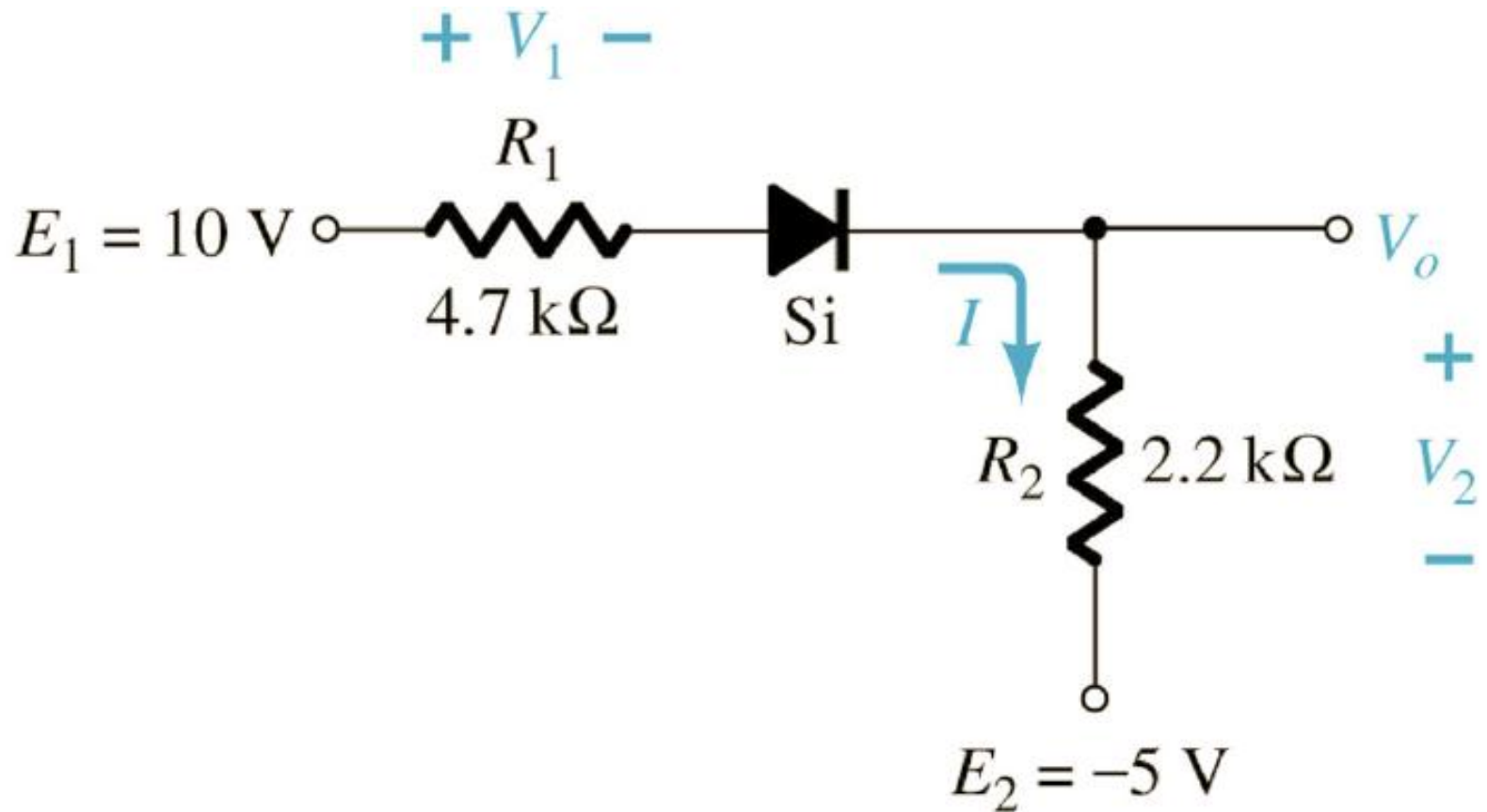
# Circuitos série de diodos



a) Quem está conduzindo (ON) e quem está bloqueado (OFF)?

b) Determine  $V_o$ ,  $I_R$  e  $V_{D_2}$ .

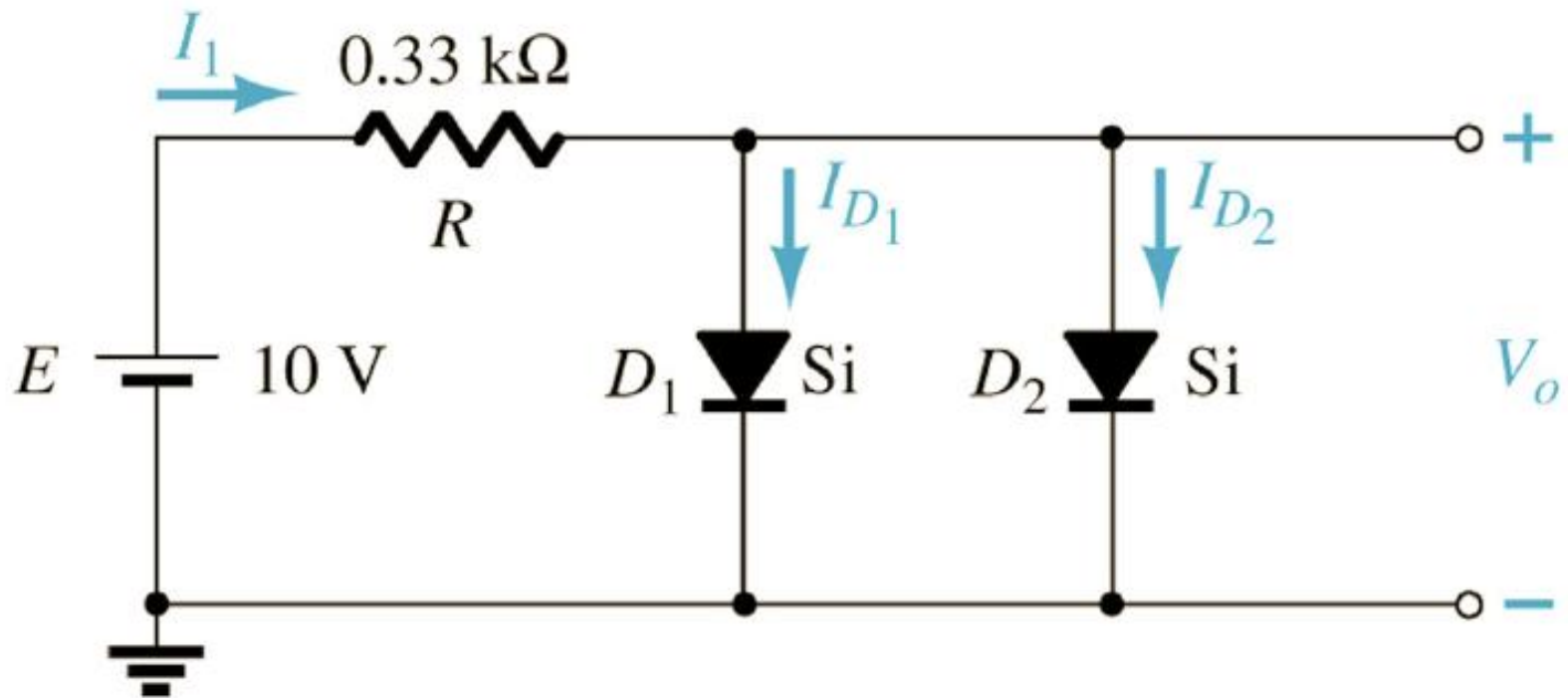
# Circuitos série de diodos



a) Diodo está ON ou OFF?

b) Determine  $V_1$ ,  $V_2$  e  $I$ .

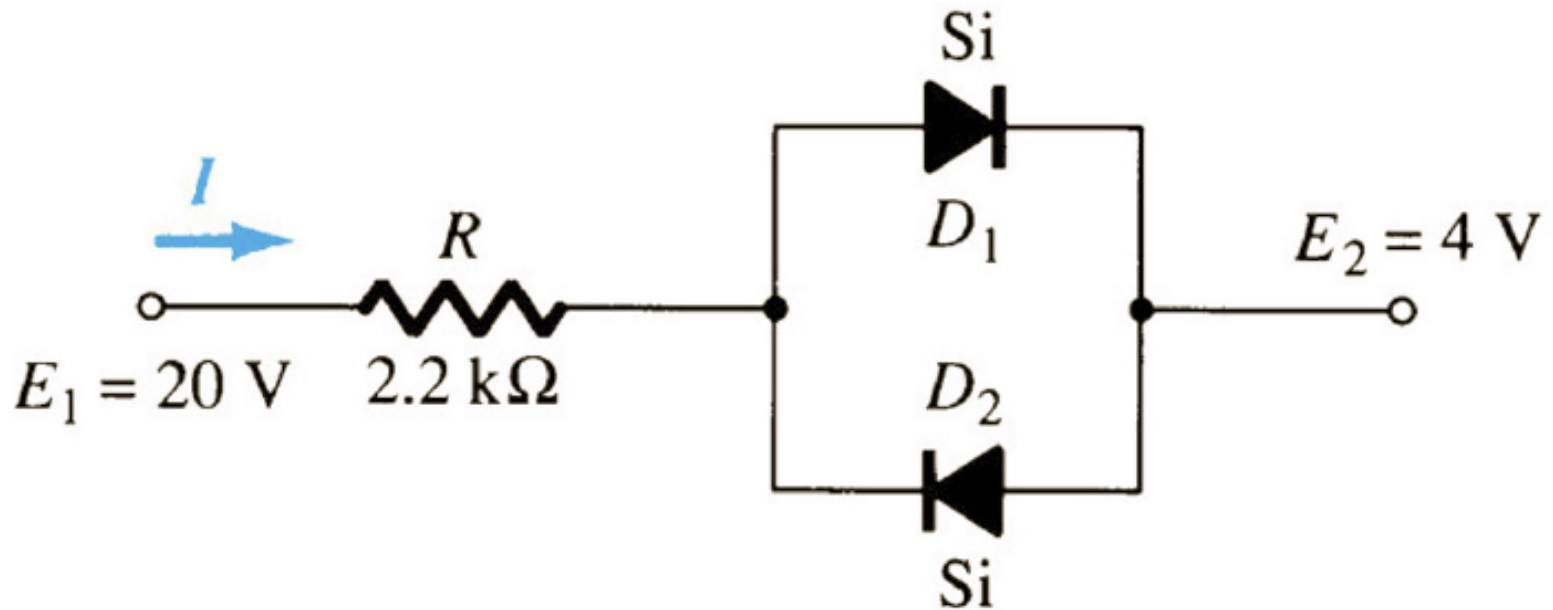
# Circuitos paralelo de diodos



a) Quem está conduzindo (ON) e quem está bloqueado (OFF)?

b) Determine  $V_o$ ,  $I_1$ ,  $I_{D1}$  e  $I_{D2}$ .

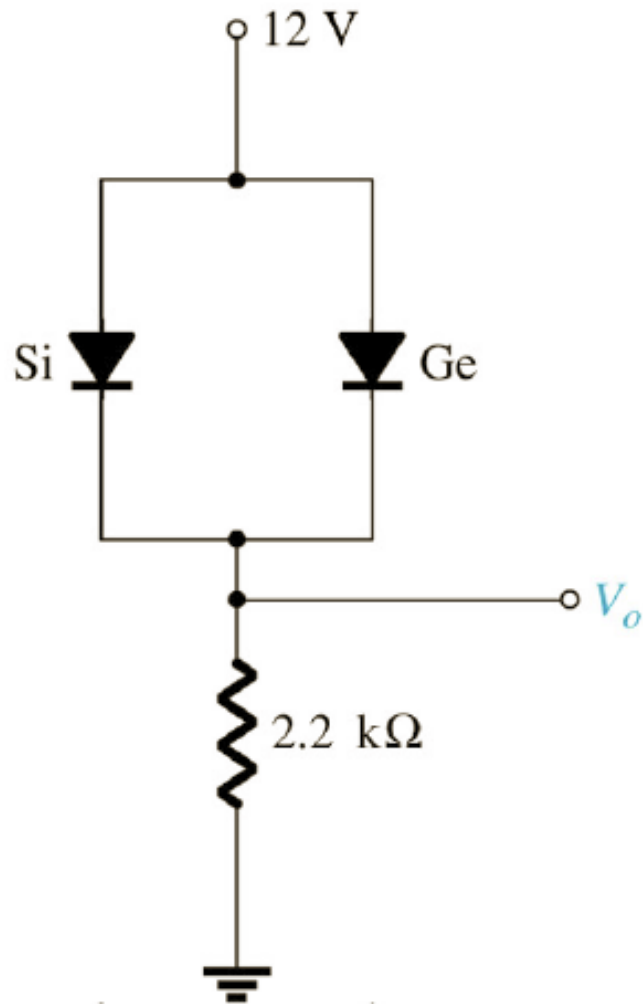
# Circuitos paralelo de diodos



a) Quem está conduzindo (ON) e quem está bloqueado (OFF)?

b) Determine  $V_o$ ,  $I_1$ ,  $I_{D1}$  e  $I_{D2}$ .

# Circuitos paralelo de diodos

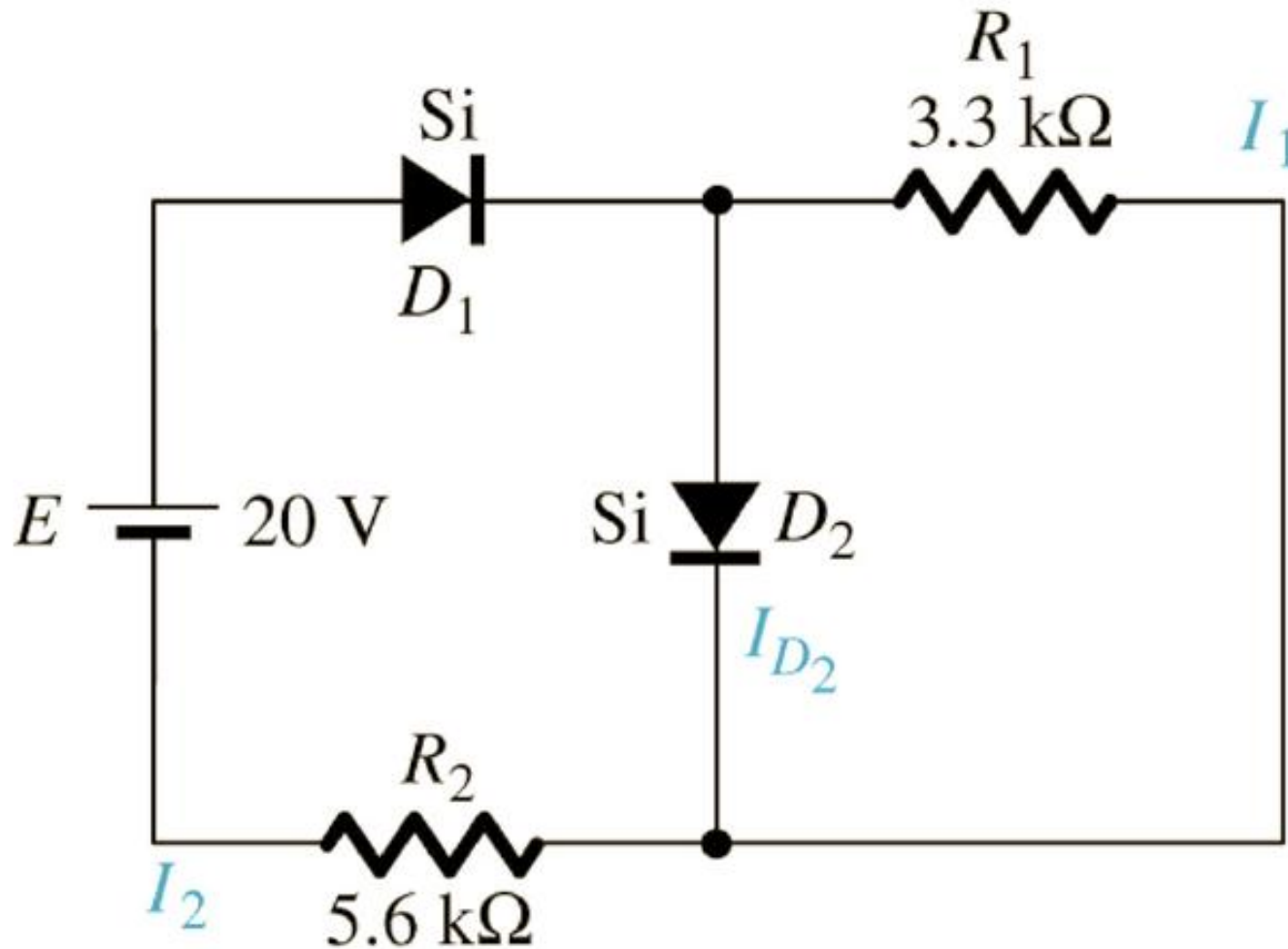


a) Quem está conduzindo (ON) e quem está bloqueado (OFF)?

b) Determine  $V_o$ ,  $I_1$ ,  $I_{D1}$  e  $I_{D2}$ .

# Circuitos paralelo de diodos

Exemplo 2.15: Determinar as correntes  $I_1$ ,  $I_2$  e  $I_{D2}$ .



# Próxima aula

## **Seqüência de conteúdos:**

1. Análise de circuitos com diodos.